ACGI020022-P43-1

S-band matched GaAs Device

Features:

Frequency: 2~2.2GHz

1dB Output Power : P_{1dB}≥43dBm

PowerGain: Gain≥10.5dB

Efficiency: η=45%（type）

Port matching: Z_{in}/Z_{out}=50Ω

Description:

ACGI020022-P43-1 is an internal matching GaAs device, which adopts advanced co-planar internal matching MCM and thin film circuit technology. The typical working frequency range is 2~2.2GHz. This device can be used in different RF/Microwave system and subsystem. The high output power level, high efficiency and wide operating temperature range can make application very flexible.

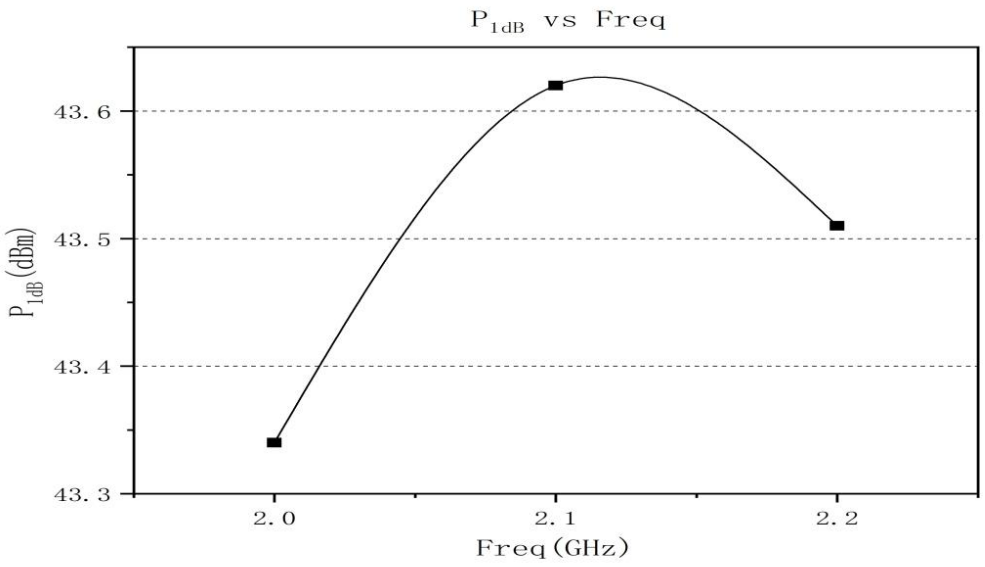
Maximun Ratings (TC=25℃, Not recommended working under this condition):

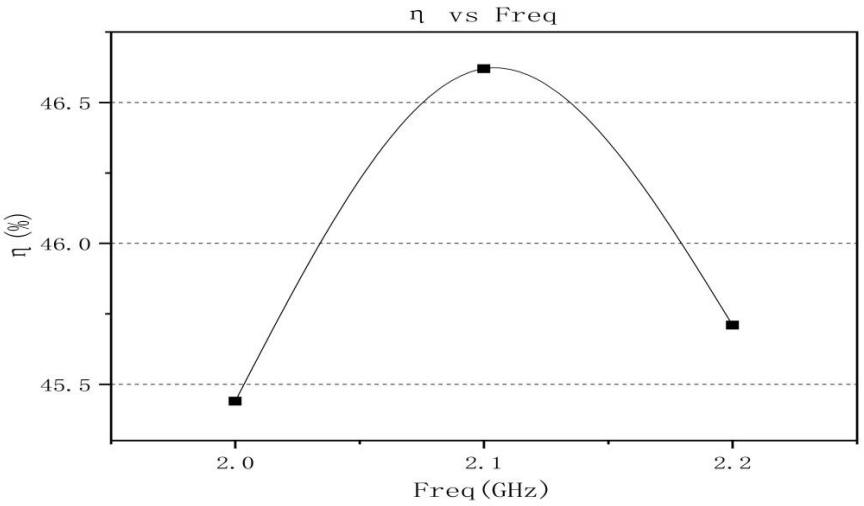
	Symbol	Value	Unit
Voltage between source and drain	V_{ds}	11	V
Voltage between gate and source	V_{gs}	-3	V
Storage Temperature Range	T_{stg}	-65 to +150	℃
Drain and Source Channel Temperature	T_{ch}	150	℃

Electrical Characteristics:

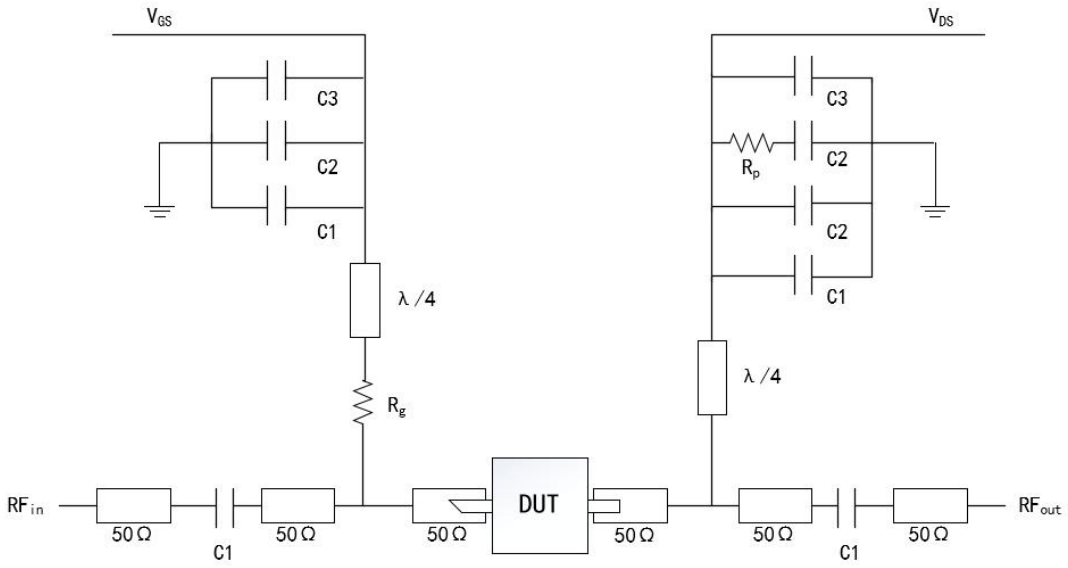
	Symbol	Test condition	Value			Unit
			Min	Typ	Max	
Drain Current	I_{dsr}	Vds=10V CW. Pin: 32.5dBm Freq: 2~2.2GHz	-	4.4	-	A
1dB output power	P_{1dB}		43	-	-	dBm
Gain	G_p		10.5	-	-	dB
Efficiency	η		-	45	-	%
Gain Flatness	ΔG		-0.8	-	+0.8	dB

Typical Curve:





Application Circuit:



DUT: Device to be tested

C1:8pF

C2:1000pF

C3:100uF

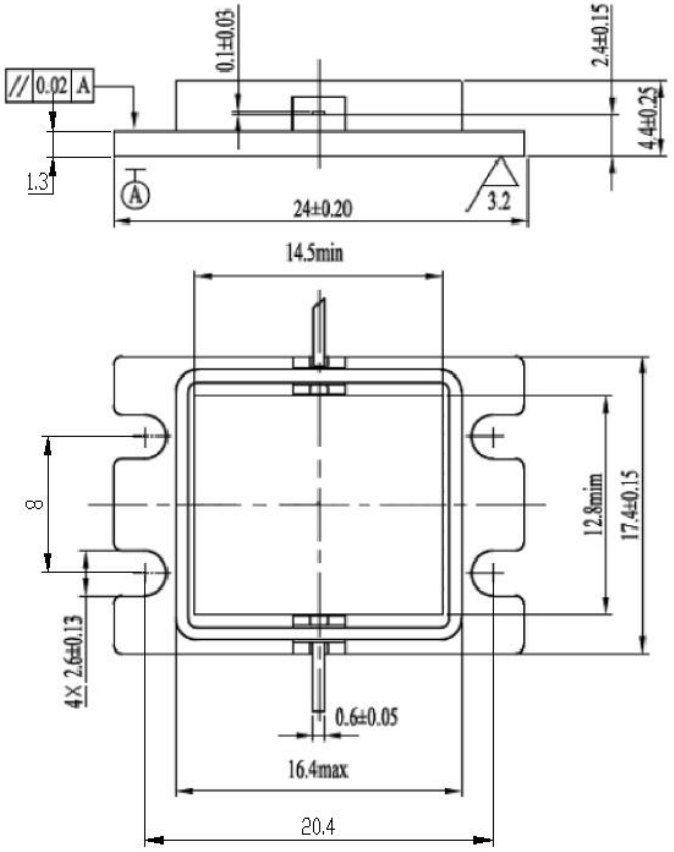
R_P:51Ω

R_G:15Ω

ESD Level:

ESD	Class III	2000V

Outline:



Precautions for use:

- Pay attention to drying transportation and storage.
- Pay attention to anti-static during chip use and assembly，and wear grounding anti-static bracelet.
- When powering up，first apply grid power then add leakage.